

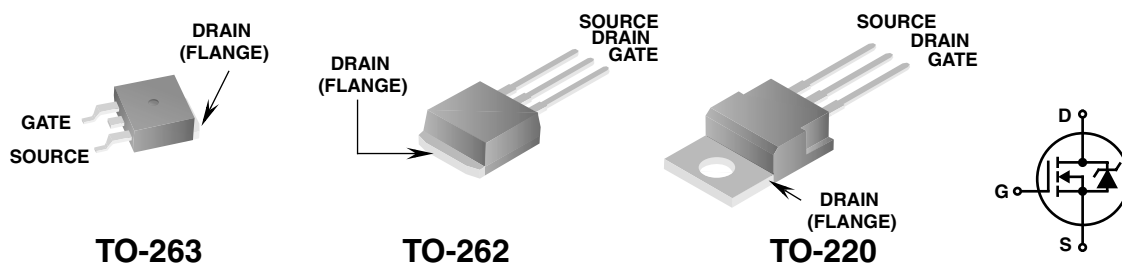
IRF640N/IRF640NS/IRF640NL

N-Channel Power MOSFETs 200V, 18A, 0.15Ω

Features

- Ultra Low On-Resistance
 - $r_{DS(ON)} = 0.102\Omega$ (Typ), $V_{GS} = 10V$
- Simulation Models
 - Temperature Compensated PSpice® and SABER® Electrical Models
 - Spice and SABER® Thermal Impedance Models

- Peak Current vs Pulse Width Curve
- UIS Rating Curve



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	200	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current		
	Continuous ($T_C = 25^\circ\text{C}$, $V_{GS} = 10V$)	18	A
	Continuous ($T_C = 100^\circ\text{C}$, $V_{GS} = 10V$)	13	A
	Pulsed	Figure 4	A
E_{AS}	Single Pulse Avalanche Energy (Note 1)	247	mJ
P_D	Power dissipation	150	W
	Derate above 25°C	1.0	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case TO-220, TO-262, TO-263	1.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-220, TO-262, TO-263	62	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-263, 1in ² copper pad area	40	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
640N	IRF640NS	TO-263AB	330mm	24mm	800 units
640N	IRF640NL	TO-262AA	Tube	N/A	50
640N	IRF640N	TO-220AB	Tube	N/A	50

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

$B_{V_{DS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	200	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{V}$, $V_{GS} = 0\text{V}$ $V_{DS} = 160\text{V}$, $T_C = 150^\circ$	-	-	25 250	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(TH)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2	-	4	V
$r_{DS(ON)}$	Drain to Source On Resistance	$I_D = 11\text{A}$, $V_{GS} = 10\text{V}$	-	0.102	0.15	Ω
g_{fs}	Forward Transconductance	$V_{DS} = 50\text{V}$, $I_D = 11\text{A}$ (Note 2)	6.8	-	-	S

Dynamic Characteristics

C_{ISS}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	2200	-	pF
C_{OSS}	Output Capacitance		-	400	-	pF
C_{RSS}	Reverse Transfer Capacitance		-	120	-	pF
$Q_{g(TOT)}$	Total Gate Charge at 20V	$V_{GS} = 0\text{V}$ to 20V	$V_{DD} = 100\text{V}$ $I_D = 22\text{A}$ $I_g = 1.0\text{mA}$	117	152	nC
$Q_{g(10)}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V}$ to 10V		64	83	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0\text{V}$ to 2V		5	7	nC
Q_{gs}	Gate to Source Gate Charge			9	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			24	-	nC

Switching Characteristics ($V_{GS} = 10\text{V}$)

t_{ON}	Turn-On Time	$V_{DD} = 100\text{V}$, $I_D = 11\text{A}$ $V_{GS} = 10\text{V}$, $R_{GS} = 2.5\Omega$	-	-	44	ns
$t_{d(ON)}$	Turn-On Delay Time		-	10	-	ns
t_r	Rise Time		-	19	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time		-	23	-	ns
t_f	Fall Time		-	5.5	-	ns
t_{OFF}	Turn-Off Time		-	-	46	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 11\text{A}$	-	-	1.3	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 11\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	251	ns
Q_{RR}	Reverse Recovered Charge	$I_{SD} = 11\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	1394	nC

Notes:

- 1: Starting $T_J = 25^\circ\text{C}$, $L = 4.2\text{mH}$, $I_{AS} = 11\text{A}$.
- 2: Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.

Typical Characteristic

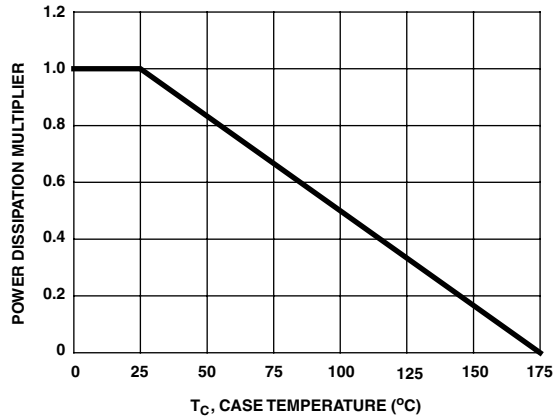


Figure 1. Normalized Power Dissipation vs Ambient Temperature

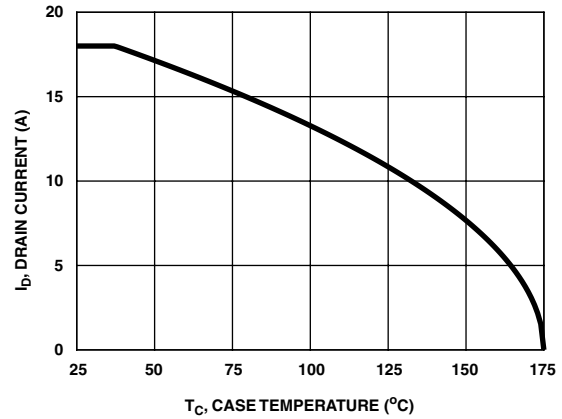


Figure 2. Maximum Continuous Drain Current vs Case Temperature

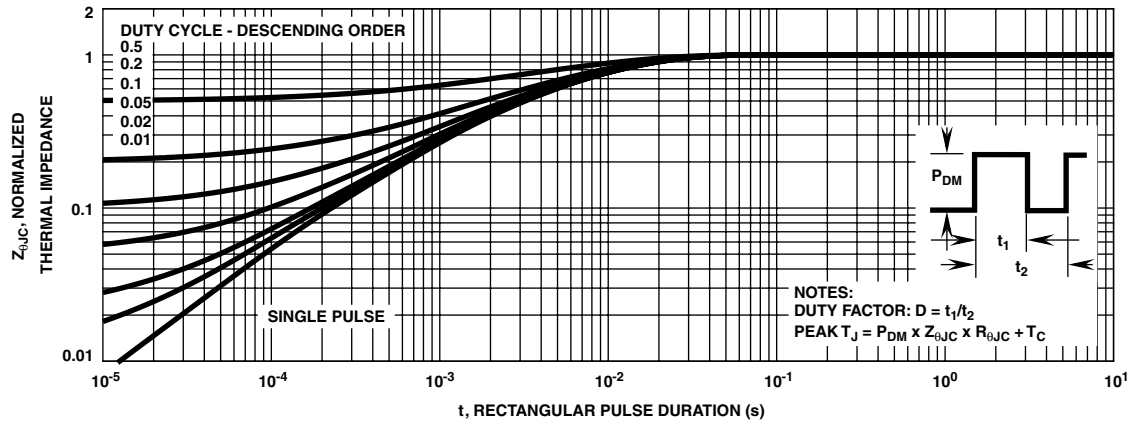


Figure 3. Normalized Maximum Transient Thermal Impedance

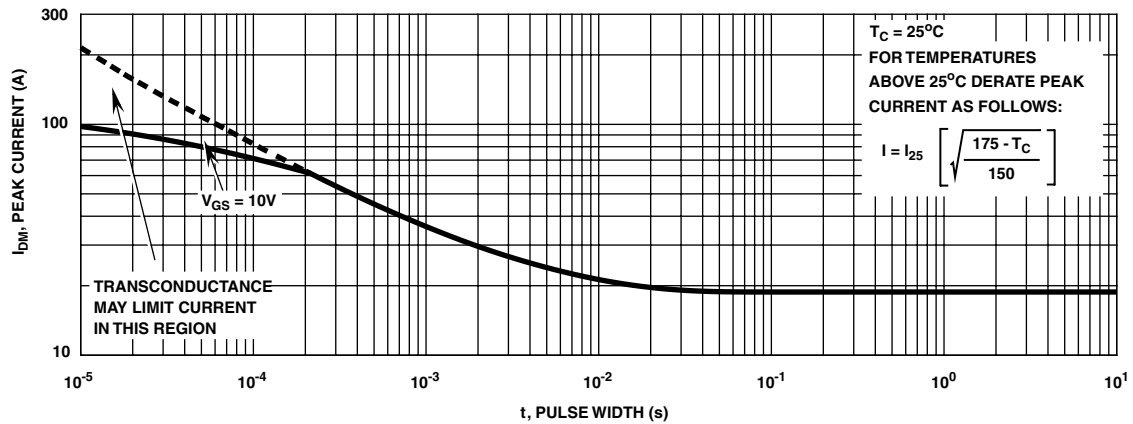


Figure 4. Peak Current Capability

Typical Characteristic (Continued)

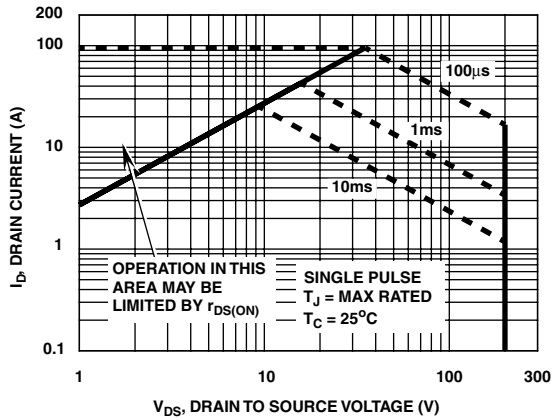


Figure 5. Forward Bias Safe Operating Area

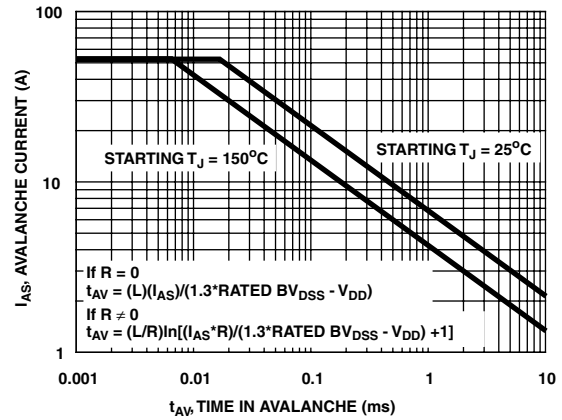


Figure 6. Unclamped Inductive Switching Capability

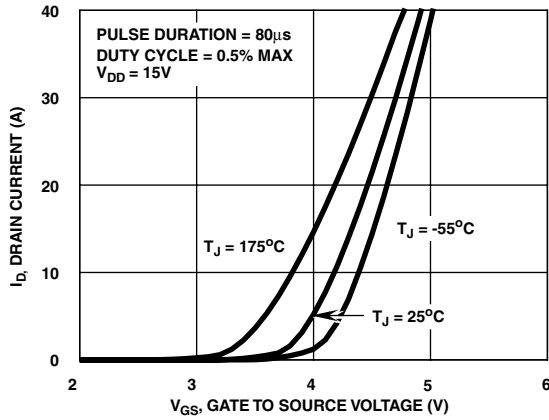


Figure 7. Transfer Characteristics

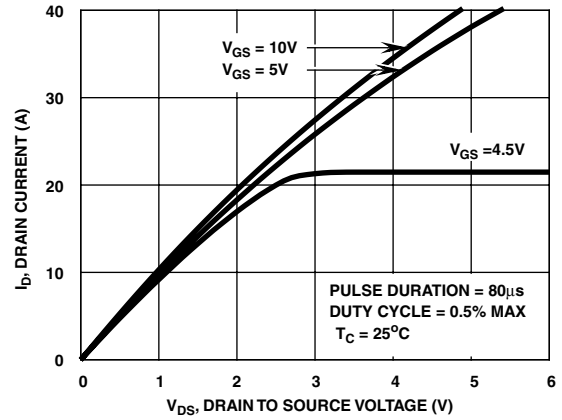


Figure 8. Saturation Characteristics

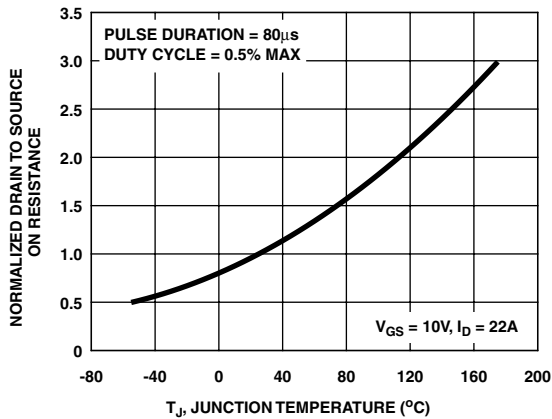


Figure 9. Normalized Drain To Source On Resistance vs Junction Temperature

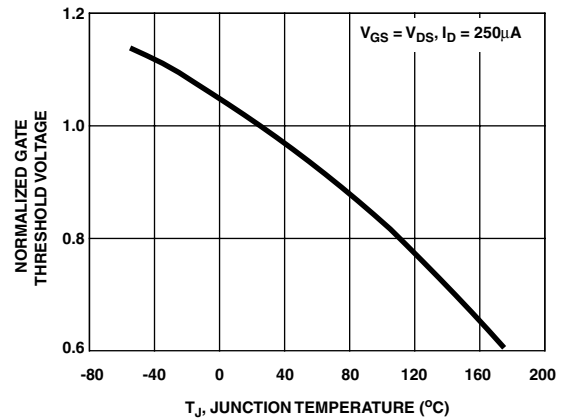


Figure 10. Normalized Gate Threshold Voltage vs Junction Temperature

Typical Characteristic (Continued)

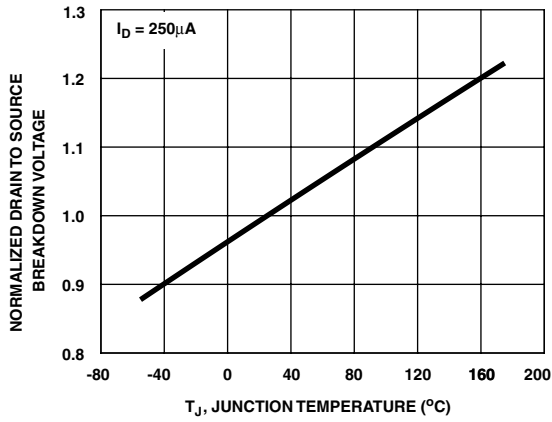


Figure 11. Normalized Drain To Source Breakdown Voltage vs Junction Temperature

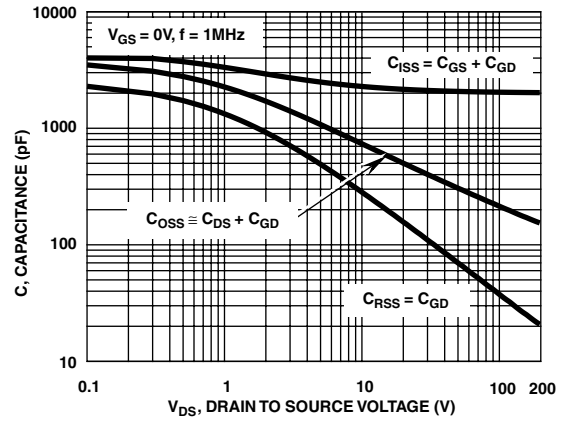


Figure 12. Capacitance vs Drain to Source Voltage

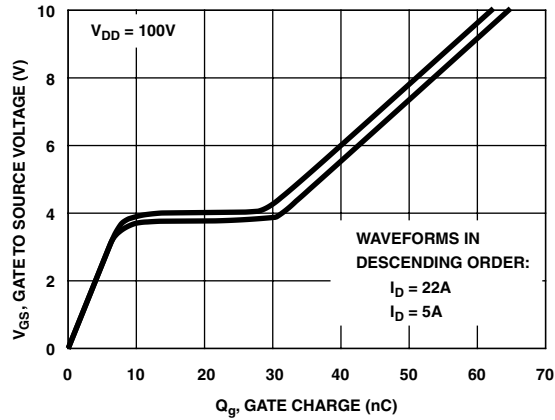


Figure 13. Gate Charge Waveforms for Constant Gate Currents

Test Circuits and Waveforms

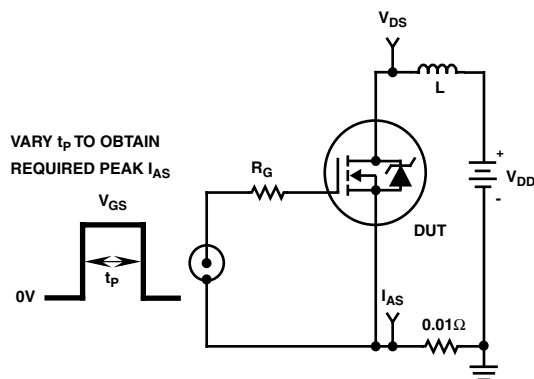


Figure 14. Unclamped Energy Test Circuit

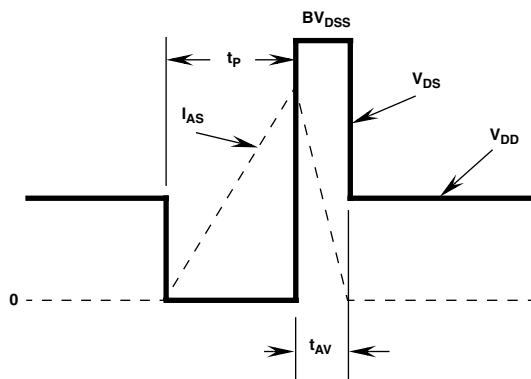


Figure 15. Unclamped Energy Waveforms

Test Circuits and Waveforms (Continued)

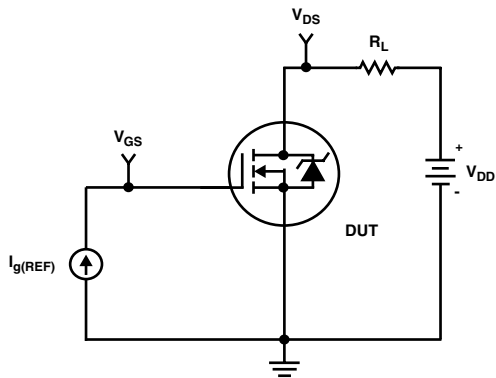


Figure 16. Gate Charge Test Circuit

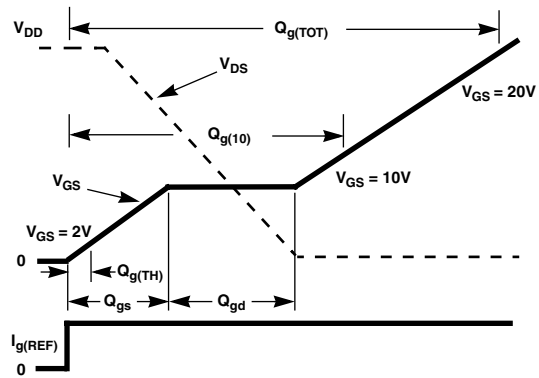


Figure 17. Gate Charge Waveforms

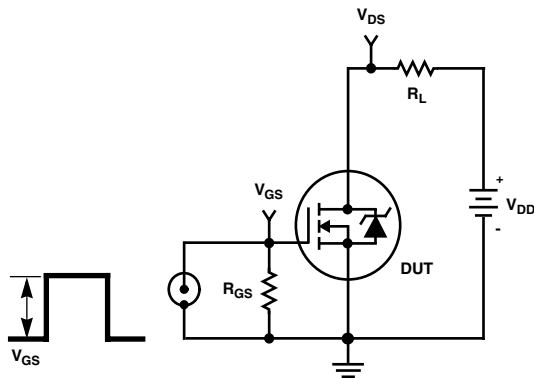


Figure 18. Switching Time Test Circuit

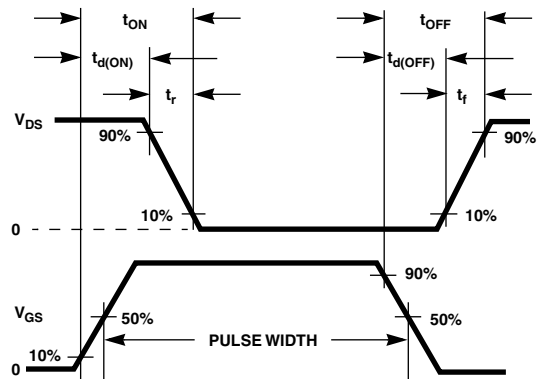


Figure 19. Switching Time Waveforms

Thermal Resistance vs. Mounting Pad Area

The maximum rated junction temperature, T_{JM} , and the thermal resistance of the heat dissipating path determines the maximum allowable device power dissipation, P_{DM} , in an application. Therefore the application's ambient temperature, T_A ($^{\circ}\text{C}$), and thermal resistance $R_{\theta JA}$ ($^{\circ}\text{C}/\text{W}$) must be reviewed to ensure that T_{JM} is never exceeded. Equation 1 mathematically represents the relationship and serves as the basis for establishing the rating of the part.

$$P_{DM} = \frac{(T_{JM} - T_A)}{Z_{\theta JA}} \quad (\text{EQ. 1})$$

In using surface mount devices such as the TO-263 package, the environment in which it is applied will have a significant influence on the part's current and maximum power dissipation ratings. Precise determination of P_{DM} is complex and influenced by many factors:

1. Mounting pad area onto which the device is attached and whether there is copper on one side or both sides of the board.
2. The number of copper layers and the thickness of the board.
3. The use of external heat sinks.
4. The use of thermal vias.
5. Air flow and board orientation.
6. For non steady state applications, the pulse width, the duty cycle and the transient thermal response of the part, the board and the environment they are in.

Fairchild provides thermal information to assist the designer's preliminary application evaluation. Figure 20 defines the $R_{\theta JA}$ for the device as a function of the top copper (component side) area. This is for a horizontally positioned FR-4 board with 1oz copper after 1000 seconds of steady state power with no air flow. This graph provides the necessary information for calculation of the steady state junction temperature or power dissipation. Pulse applications can be evaluated using the Fairchild device Spice thermal model or manually utilizing the normalized maximum transient thermal impedance curve.

Displayed on the curve are $R_{\theta JA}$ values listed in the Electrical Specifications table. The points were chosen to depict the compromise between the copper board area, the thermal resistance and ultimately the power dissipation, P_{DM} .

Thermal resistances corresponding to other copper areas can be obtained from Figure 20 or by calculation using Equation 2. $R_{\theta JA}$ is defined as the natural log of the area times a coefficient added to a constant. The area, in square inches is the top copper area including the gate and source pads.

$$R_{\theta JA} = 26.51 + \frac{19.84}{(0.262 + \text{Area})} \quad (\text{EQ. 2})$$

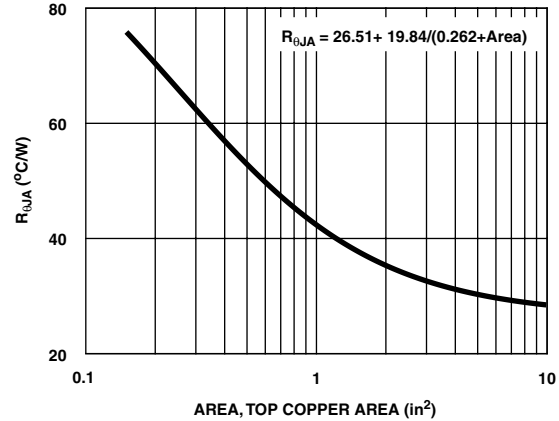


Figure 20. Thermal Resistance vs Mounting Pad Area

PSPICE Electrical Model

.SUBCKT IRF640N 2 1 3 ; rev 10 October 2000

CA 12 8 3.6e-9
CB 15 14 3.5e-9
CIN 6 8 2e-9

DBODY 7 5 DBODYMOD
DBREAK 5 11 DBREAKMOD
DPLCAP 10 5 DPLCAPMOD

EBREAK 11 7 17 18 225
EDS 14 8 5 8 1
EGS 13 8 6 8 1
ESG 6 10 6 8 1
EVTHRES 6 21 19 8 1
EVTEMP 20 6 18 22 1

IT 8 17 1

LDRAIN 2 5 1e-9
LGATE 1 9 5.78e-9
LSOURCE 3 7 3.92e-9

MMED 16 6 8 8 MMEDMOD
MSTRO 16 6 8 8 MSTROMOD
MWEAK 16 21 8 8 MWEAKMOD

RBREAK 17 18 RBREAKMOD 1
RDRAIN 50 16 RDRAINMOD 83.5e-3
RGATE 9 20 7.6e-1
RLDRAIN 2 5 10
RLGATE 1 9 57.8
RLSOURCE 3 7 39.2
RSLC1 5 51 RSLCMOD 1e-6
RSLC2 5 50 1e3
RSOURCE 8 7 RSOURCEMOD 10e-3
RVTHRES 22 8 RVTHRESMOD 1
RVTEMP 18 19 RVTEMPMOD 1

S1A 6 12 13 8 S1AMOD
S1B 13 12 13 8 S1BMOD
S2A 6 15 14 13 S2AMOD
S2B 13 15 14 13 S2BMOD

VBAT 22 19 DC 1

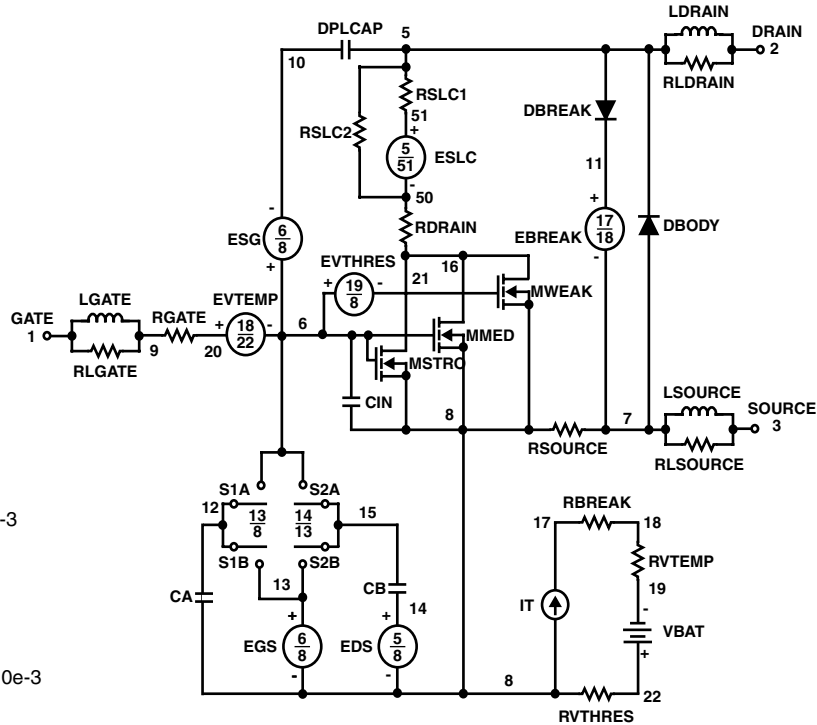
ESLC 51 50 VALUE={(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)/(1e-6*38),2.5))}

.MODEL DBODYMOD D (IS = 1.2e-12 RS = 5.5e-3
XTI = 5.5 TRS1 = 1e-5 TRS2 = 8e-6 + CJO = 12.5e-10 TT = 1e-7 M = 0.42)
.MODEL DBREAKMOD D (RS = 2.5 TRS1 = 1e-3 TRS2 = -8.9e-6)
.MODEL DPLCAPMOD D (CJO = 2.5e-9 IS = 1e-30 N = 10 M = 0.9)
.MODEL MMEDMOD NMOS (VTO = 3.14 KP = 5 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 7.6e-1)
.MODEL MSTROMOD NMOS (VTO = 3.68 KP = 100 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)
.MODEL MWEAKMOD NMOS (VTO = 2.76 KP = 0.05 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 7.6 RS = 0.1)
.MODEL RBREAKMOD RES (TC1 = 1.52e-3 TC2 = -2e-7)
.MODEL RDRAINMOD RES (TC1 = 9.8e-3 TC2 = 2.6e-5)
.MODEL RSLCMOD RES (TC1 = 3e-3 TC2 = 1e-6)
.MODEL RSOURCEMOD RES (TC1 = 1e-3 TC2 = 1e-6)
.MODEL RVTHRESMOD RES (TC1 = -2.3e-3 TC2 = -1.3e-5)
.MODEL RVTEMPMOD RES (TC1 = -2.8e-3 TC2 = 1.7e-6)

.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -8.5 VOFF = -1)
.MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -1 VOFF = -8.5)
.MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -0.1 VOFF = 0.2)
.MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0.2 VOFF = -0.1)

.ENDS

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.



IRF640N/IRF640NS/IRF640NL

SPICE Thermal Model

REV 10 October 2000
IRF640N

CTHERM1 th 6 2.8e-3
CTHERM2 6 5 4.6e-3
CTHERM3 5 4 5.5e-3
CTHERM4 4 3 9.2e-3
CTHERM5 3 2 1.7e-2
CTHERM6 2 tl 4.3e-2

RTHERM1 th 6 5e-4
RTHERM2 6 5 1.5e-3
RTHERM3 5 4 2e-2
RTHERM4 4 3 9e-2
RTHERM5 3 2 1.9e-1
RTHERM6 2 tl 2.9e-1

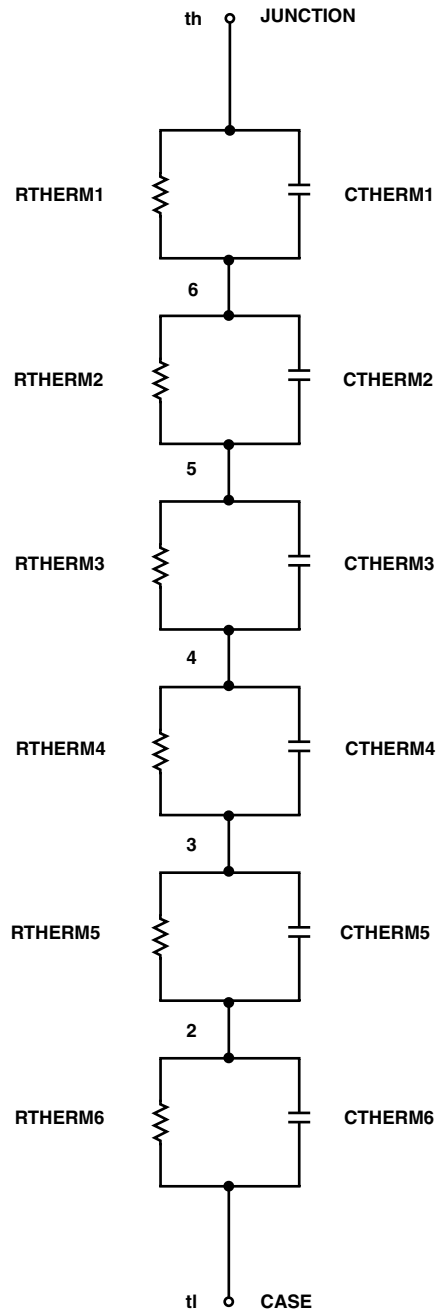
SABER Thermal Model

IRF640N

template thermal_model th tl
thermal_c th, tl

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  ctherm.ctherm2 6 5 = 4.6e-3
  ctherm.ctherm3 5 4 = 5.5e-3
  ctherm.ctherm4 4 3 = 9.2e-3
  ctherm.ctherm5 3 2 = 1.7e-2
  ctherm.ctherm6 2 tl = 4.3e-2
}
```

```
rtherm.rtherm1 th 6 = 5e-4
rtherm.rtherm2 6 5 = 1.5e-3
rtherm.rtherm3 5 4 = 2e-2
rtherm.rtherm4 4 3 = 9e-2
rtherm.rtherm5 3 2 = 1.9e-1
rtherm.rtherm6 2 tl = 2.9e-1
}
```



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CoolFET TM	FRFET TM	PACMAN TM	Stealth TM	
CROSSVOLT TM	GlobalOptoisolator TM	POP TM	SuperSOT TM -3	
DenseTrench TM	GTO TM	Power247 TM	SuperSOT TM -6	
DOME TM	HiSeC TM	PowerTrench [®]	SuperSOT TM -8	
EcoSPARK TM	ISOPLANAR TM	QFET TM	SyncFET TM	
E ² CMOS TM	LittleFET TM	QS TM	TinyLogic TM	
EnSigna TM	MicroFET TM	QT Optoelectronics TM	TruTranslation TM	
FACT TM	MicroPak TM	Quiet Series TM	UHC TM	
FACT Quiet Series TM	MICROWIRE TM	SILENT SWITCHER [®]	UltraFET [®]	

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PRODUCT STATUS DEFINITIONS

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Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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